

Fourfold Symmetry of Anisotropic Magnetoresistance in Epitaxial Fe₃O₄ Thin Films

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I.INTRODUCTION

 \blacklozenge In high quality epitaxial Fe₃O₄ films grown on MgO(001) substrates, the Planar Hall effect (PHE) contains only a twofold angular dependence, but the anisotropic magnetoresistance (AMR) below 200K is constituted with both twofold and fourfold symmetric terms. The origin of the four-fold symmetry of AMR is either due to the symmetry of the lattice or the spin scattering near the antiphase

Sample:

- 1. MgO(001) substrate annealing at 600°C 10nm seed layer was grown at 500 °C.
- 2. Evaporating the Fe atoms at an oxygen pressure of $\sim 1 \times 10^{-5}$ Torr.
- 3. Patterned into the Hall geometry by two-step lithography.
- Measurement:



RHEED pattern of Fe_3O_4

II. EXPERIMENT STEPS



boundaries(APBs)?

Physical Property Measurement System



 $\rho_{\rm xv} = C_U^{PHE} \cos(\theta - \theta_U^{PHE}) + C_4 \sin\theta \cos\theta$

V. Out-plan AMR

IV. Antiphase boundaries(APBs)



Celotto, et. al., Eur. hys. J. B 36, 271(2003)

- 150 K - 120 K Four-fold is single rystal Fe₃O₄. R. Ramos, et. al., Phys. Rev. B 78, 214402 (2008). 280 320



Magnetic field rotational plan perpendicular to the current

AMR amplitude is quite The similar in both in-plan and out-plan measurements which indicates the four-fold symmetry of AMR is related to the cubic crystalline structure.





